

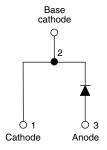
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Vishay Semiconductors

# HEXFRED® Ultrafast Soft Recovery Diode, 25 A



TO-247AC 2L



PRIMARY CHARACTERISTICS					
I <sub>F(AV)</sub>	25 A				
$V_{R}$	600 V				
V <sub>F</sub> at I <sub>F</sub>	1.3 V				
t <sub>rr</sub> (yp.	23 ns				
T <sub>J</sub> max.	150 °C				
Package	TO-247AC 2L				
Circuit configuration	Single				

#### **FEATURES**

- Ultrafast and ultrasoft recovery
- Very low I<sub>RBM</sub> and Q<sub>rr</sub>
- Designed and qualified according to JEDEC®-JESD 47





ROHS COMPLIANT HALOGEN FREE

#### **BENEFITS**

- Reduced RFI and EMI
- · Reduced power loss in diode and switching transistor
- · Higher frequency operation
- · Reduced snubbing
- · Reduced parts count

#### **DESCRIPTION**

VS-HFA25PB60... is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 600 V and 25 A continuous current, the VS-HFA25PB60... is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I<sub>RRM</sub>) and does not exhibit any tendency to "snap-off" during the th portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA25PB60... is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Cathode to anode voltage	V <sub>R</sub>		600	V		
Maximum continuous forward current	I <sub>F</sub>	T <sub>C</sub> = 100 °C	25			
Single pulse forward current	I <sub>FSM</sub>	t <sub>p</sub> = 10 ms	225	Α		
Maximum repetitive forward current	I <sub>FRM</sub>		100			
Maximum power dissipation	P <sub>D</sub>	T <sub>C</sub> = 25 °C	151	W		
waximum power dissipation		T <sub>C</sub> = 100 °C	60	- vv		
Operating junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-55 to +150	°C		



<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Cathode to anode breakdown voltage	V <sub>BR</sub>	Ι <sub>R</sub> = 100 μΑ		600	-	-	
		I <sub>F</sub> = 25 A	See fig. 1	-	1.3	1.7	V
Maximum forward voltage	V <sub>FM</sub>	I <sub>F</sub> = 50 A		-	1.5	2.0	
		I <sub>F</sub> = 25 A, T <sub>J</sub> = 125 °C		-	1.3	1.7	
Maximum reverse	_	$V_R = V_R$ rated	See fig. 2	-	1.5	20	
leakage current	I <sub>RM</sub>	$T_J = 125$ °C, $V_R = 0.8 \times V_R$ rated	See lig. 2	-	600	2000	μΑ
Junction capacitance	C <sub>T</sub>	V <sub>R</sub> = 200 V	See fig. 3	-	55	100	pF
Series inductance	LS	Measured lead to lead 5 mm from package body		-	12	-	nH

<b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS	
	t <sub>rr</sub>	$I_F = 1.0 \text{ A}, dI_F/dt = 200 \text{ A}$	A/μs, V <sub>R</sub> = 30 V	-	23	-	
Reverse recovery time See fig. 5, 10	t <sub>rr1</sub>	T <sub>J</sub> = 25 °C		-	50	75	ns
See lig. 5, 10	t <sub>rr2</sub>	T <sub>J</sub> = 125 °C	I <sub>F</sub> = 25 A	-	105	160	
Peak recovery current	I <sub>RRM1</sub>	T <sub>J</sub> = 25 °C		-	4.5	10	А
See fig. 6, 10	I <sub>RRM2</sub>	T <sub>J</sub> = 125 °C		-	8.0	15	
Reverse recovery charge	Q <sub>rr1</sub>	T <sub>J</sub> = 25 °C	dI <sub>F</sub> /dt = 200 A/μs	-	112	375	nC
See fig. 7, 10	Q <sub>rr2</sub>	T <sub>J</sub> = 125 °C	V <sub>R</sub> = 200 V	-	420	1200	IIC
Peak rate of fall of recovery current during t <sub>b</sub> See fig. 8, 10	dI <sub>(rec)M</sub> /dt1	T <sub>J</sub> = 25 °C		-	250	-	- A/µs
	dI <sub>(rec)M</sub> /dt2	T <sub>J</sub> = 125 °C		-	160	-	Ανμδ

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Lead temperature	T <sub>lead</sub>	0.063" from case (1.6 mm) for 10 s	-	-	300	°C	
Thermal resistance, junction to case	R <sub>thJC</sub>		-	-	0.83		
Thermal resistance, junction to ambient	R <sub>thJA</sub>	Typical socket mount	-	-	40	K/W	
Thermal resistance, case to heatsink	R <sub>thCS</sub>	Mounting surface, flat, smooth, and greased	-	0.25	-		
Weight			-	6.0	-	g	
vveigni			-	0.21	-	oz.	
Mounting torque			6.0 (5.0)	-	12 (10)	kgf ·cm (lbf ·in)	
Marking device		Case style TO-247AC 2L	HFA25PB60				



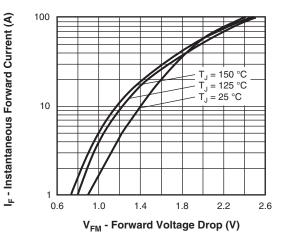


Fig. 1 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current

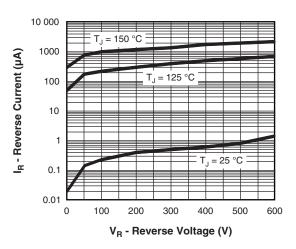


Fig. 2 - Typical Reverse Current vs. Reverse Voltage

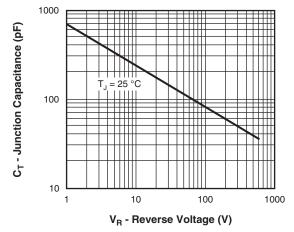


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

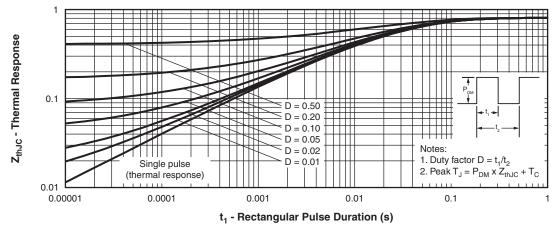


Fig. 4 - Maximum Thermal Impedance  $Z_{thJC}$  Characteristics

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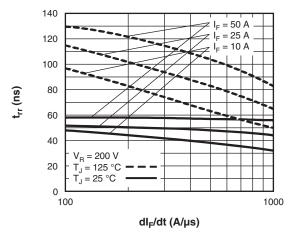


Fig. 5 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt

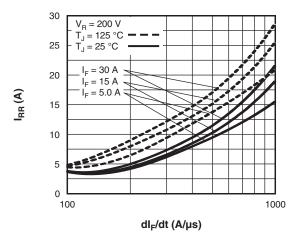


Fig. 6 - Typical Recovery Current vs. dl<sub>F</sub>/dt

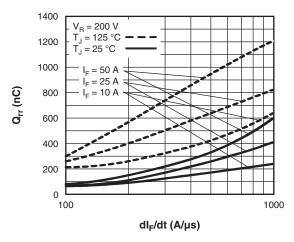


Fig. 7 - Typical Stored Charge vs. dl<sub>F</sub>/dt

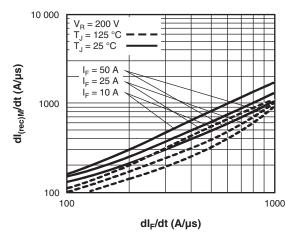
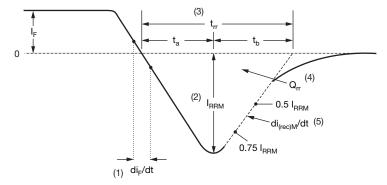


Fig. 8 - Typical  $dI_{(rec)M}/dt$  vs.  $dI_F/dt$ 



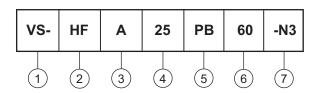
- di<sub>F</sub>/dt rate of change of current through zero crossing
- (2) I<sub>RRM</sub> peak reverse recovery current
- (3) t<sub>rr</sub> reverse recovery time measured from zero crossing point of negative going I<sub>F</sub> to point where a line passing through 0.75 I<sub>RRM</sub> and 0.50 I<sub>RRM</sub> extrapolated to zero current.
- (4)  $\mathbf{Q}_{\rm rr}$  area under curve defined by  $\mathbf{t}_{\rm rr}$  and  $\mathbf{I}_{\rm RRM}$ 
  - $Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$
- (5)  $di_{(rec)M}/dt$  peak rate of change of current during  $t_b$  portion of  $t_{rr}$

Fig. 9 - Reverse Recovery Waveform and Definitions



#### **ORDERING INFORMATION TABLE**

Device code



1 - Vishay Semiconductors product

2 - HEXFRED® family

Electron irradiated

- Current rating (25 = 25 A)

5 - PB = TO-247AC, 2 pins

6 - Voltage rating: (60 = 600 V)

7 - Environmental digit:

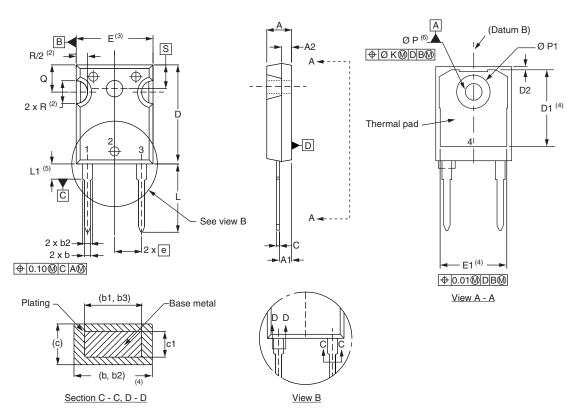
-N3 = halogen-free, RoHS-compliant, and totally lead (Pb)-free

ORDERING INFORMATION (Example)						
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION			
VS-HFA25PB60-N3	25	500	Antistatic plastic tube			

LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?96144				
Part marking information	www.vishay.com/doc?95648				
SPICE model	www.vishay.com/doc?96665				

### **TO-247AC 2L**

#### **DIMENSIONS** in millimeters and inches



SYMBOL	MILLIN	IETERS	INCHES		NOTES	
STWIBOL	MIN.	MAX.	MIN.	MAX.	NOTES	
Α	4.65	5.31	0.183	0.209		
A1	2.21	2.59	0.087	0.102		
A2	1.17	1.37	0.046	0.054		
b	0.99	1.40	0.039	0.055		
b1	0.99	1.35	0.039	0.053		
b2	1.65	2.39	0.065	0.094		
b3	1.65	2.34	0.065	0.092		
С	0.38	0.89	0.015	0.035		
c1	0.38	0.84	0.015	0.033		
D	19.71	20.70	0.776	0.815	3	
D1	13.08	-	0.515	-	4	
D2	0.51	1.35	0.020	0.053		

SYMBOL	MILLIM	IETERS	INC	HES	NOTES
OTTO	MIN.	MAX.	MIN.	MAX.	NOTES
E	15.29	15.87	0.602	0.625	3
E1	13.46	-	0.53	=.	
е	5.46	BSC	0.215	BSC	
ØΚ	0.254		0.0	)10	
L	14.20	16.10	0.559	0.634	
L1	3.71	4.29	0.146	0.169	
ØΡ	3.56	3.66	0.14	0.144	
Ø P1	-	7.39	-	0.291	
Q	5.31	5.69	0.209	0.224	
R	4.52	5.49	0.178	0.216	
S	5.51 BSC		0.217 BSC		

#### Notes

- (1) Dimensioning and tolerancing per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- $^{(7)}\,$  Outline conforms to JEDEC® outline TO-247 with exception of dimension Q



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